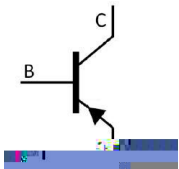


WR0<50 P M M E SQS æ M ç s ll 1 Silicon PNP transistor in a TO-92LM Plastic Package.

лъ 5VG99 : +D, Ы ´
Complementary pair with 2SD667(A).

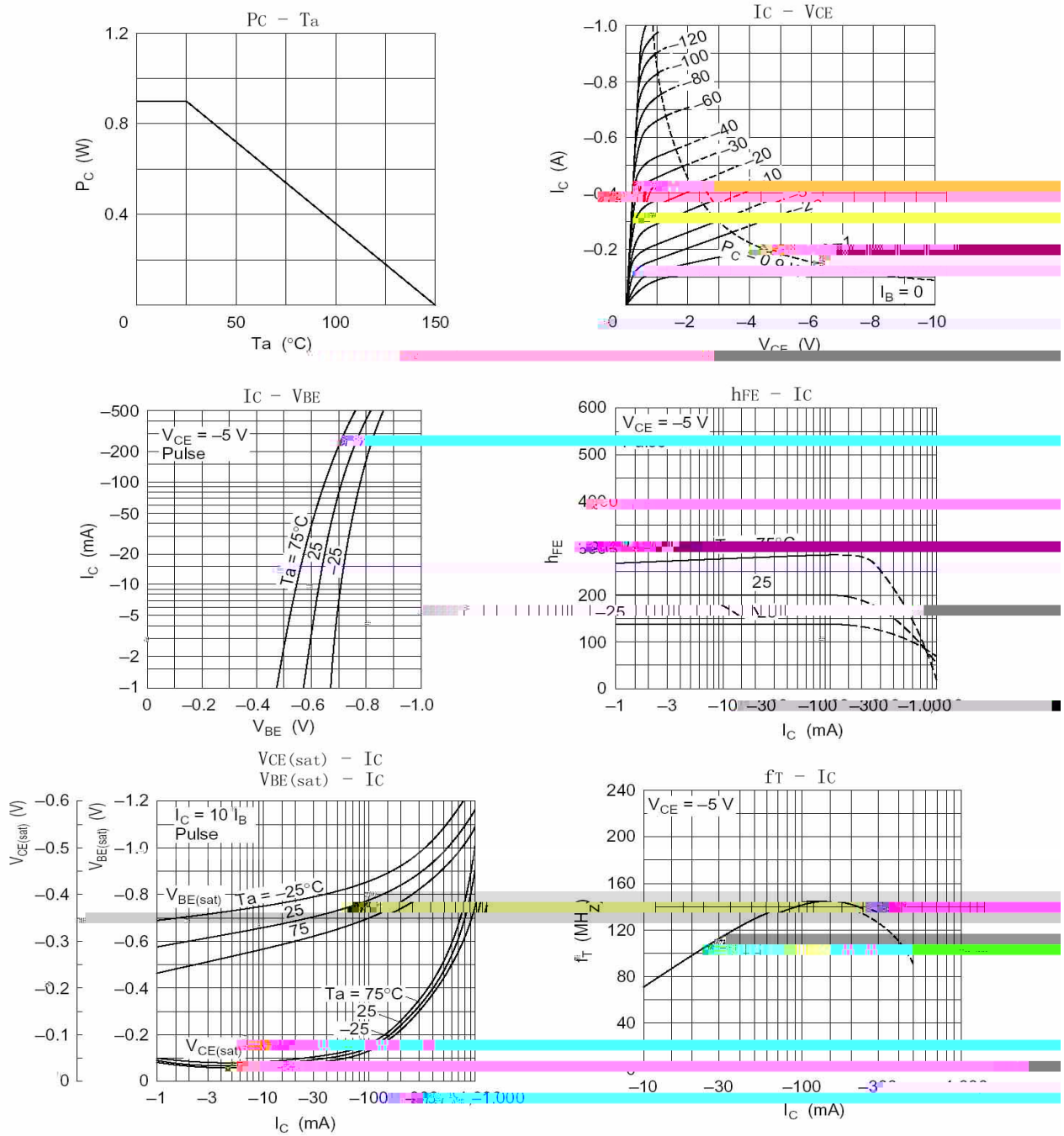
æ æ H l i ' ð z
Low frequency power amplifier.



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	2SB647 -80	V
		2SB647A -100	
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-1.0	A
Collector Current(Pulse)	I_{CP}	-2.0	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		

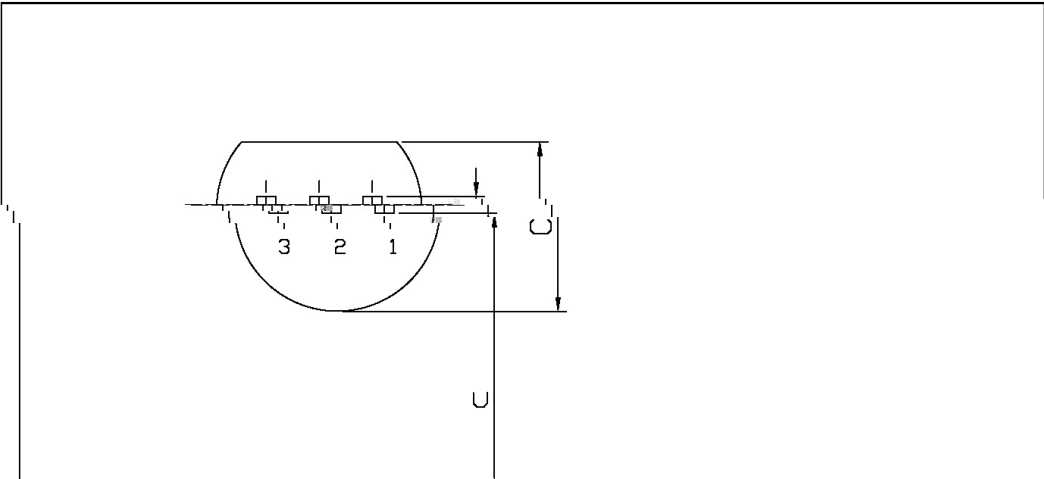
/ Electrical Characteristic Curve



/ Package Dimensions

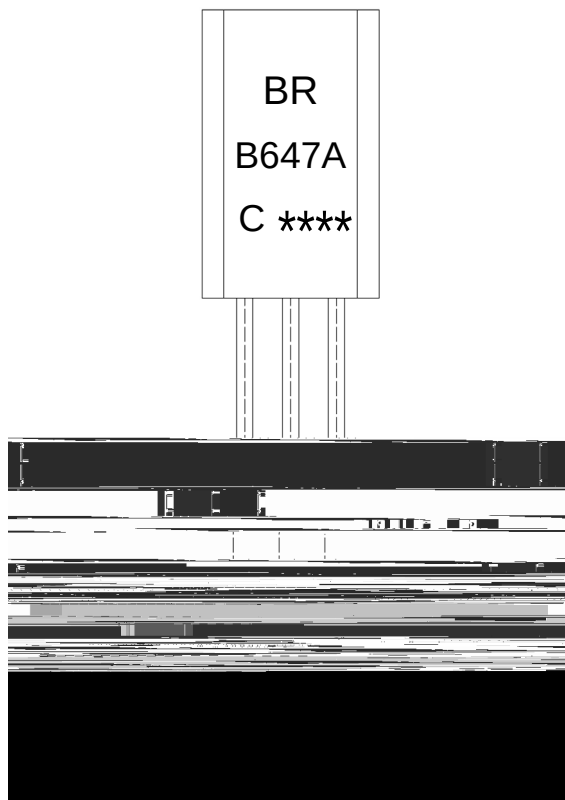
TO-92LM

Unit: mm



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.7	5.1
B	1.2	1.5
C	1.2	1.5
D	1.2	1.5
E	1.2	1.5
F	1.2	1.5
G	1.2	1.5
H	1.2	1.5
I	1.2	1.5
J	1.2	1.5
K	1.2	1.5
L	1.2	1.5
M	1.2	1.5
N	1.2	1.5
O	1.2	1.5
P	1.2	1.5
Q	1.2	1.5
R	1.2	1.5
S	1.2	1.5
T	1.2	1.5
U	1.2	1.5
V	1.2	1.5
W	1.2	1.5
X	1.2	1.5
Y	1.2	1.5
Z	1.2	1.5

/ Marking Instructions



б " X

EU: ㄣ 3 ㄴ ㄱ

E97:D X ㄣ 3 ㄴ ㄱ

F: ㄣ k_{IH} ' 6 ㄱ

---- X ㄣ 1 F ㄴ ㄴ ㄱ 1 ㄣ 1 F ㄴ ㄴ ㄱ ㄱ

Note:

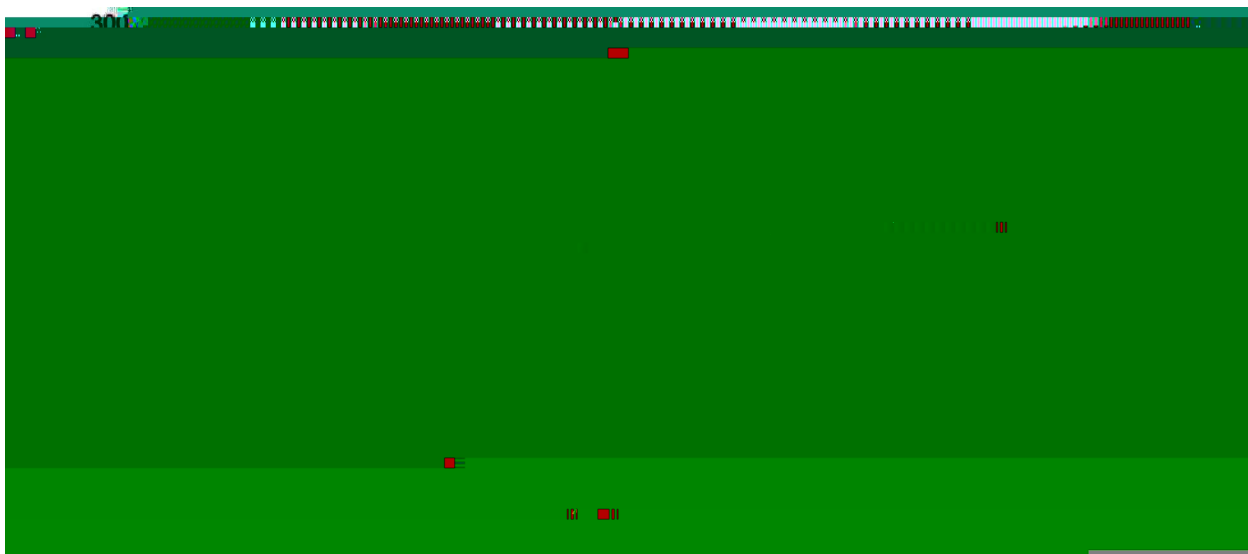
BR: Company Code.

B647A: Product Type.

C: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



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1 ١٠٠ ٢٥ ١٥٠ ٦٠ ٩٠sec;

Note:

1.Preheating:25~150 ٦